

MG25H2YS1

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		IGES	V _{GE} =±20V, V _{CE} =0	-	-	±500	nA
Collector Cut-off Current		ICES	V _{CE} =500V, V _{GE} =0	-	-	1.0	mA
Collector-Emitter Breakdown Voltage		V(BR)CES	I _C =10mA, V _{GE} =0	500	-	-	V
Gate-Emitter Cut-off Voltage		V _{GE(OFF)}	I _C =25mA, V _{CE} =5V	3.0	-	6.0	V
Collector-Emitter Saturation Voltage		V _{CE(sat)}	I _C =25A, V _{GE} =15V	-	3.5	5.0	V
Input Capacitance		C _{ies}	V _{CE} =10V, V _{GE} =0 f=1MHz	-	1500	-	pF
Switching Time	Rise Time	t _r		-	0.4	1.0	μs
	Turn-on Time	t _{on}		-	0.5	1.0	
	Fall Time	t _f		-	0.4	1.0	
	Turn-off Time	t _{off}		-	0.9	1.5	
Forward Voltage		V _F	I _F =25A, V _{GE} =0	-	1.0	2.5	V
Reverse Recovery Time		t _{rr}	I _F =25A, V _{GE} =-10V di/dt=50A/μs	-	0.3	0.5	μs
Thermal Resistance		R _{th(j-c)}	Transistor	-	-	1.00	°C/W
			Diode	-	-	1.25	





